

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): F.A. Baiocchi et al.

Case: 1-1-36-5

Serial No.: To Be Assigned

Filing Date: September 29, 2003

Group: To Be Assigned

Examiner: To Be Assigned

Title: Metal-Oxide-Semiconductor Device with
Enhanced Source Electrode

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying Form PTO-1449. A copy of each listed document is enclosed, other than the published U.S. patent document.

U.S. Patent Documents

1. U.S. Patent No. 5,869,875 issued on 02/09/99 to Hebert

Other Documents

1. C.S. Kim et al., "Trenched Sinker LDMOSFET (TS-LDMOS) Structure for High Power Amplifier Application above 2 GHz," International Electron Devices Meeting Proceedings, 2001, pp. 40.2.1-40.2.4.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability, or as a representation that no other material information exists.

Respectfully submitted,



Date: September 29, 2003

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FORM PTO-1449 (MODIFIED)**LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT**

Applicant(s): F.A. Baiocchi et al.
 Case: 1-1-36-5
 Serial No.: TBA
 Filing Date: September 29, 2003
 Group: TBA

U.S. PATENT DOCUMENTS

EXAMINER					FILING DATE
INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	IF APPROPRIATE
—	1. 5,869,875	02/09/99	Hebert		
—					

FOREIGN PATENT DOCUMENTS

EXAMINER					TRANSLATION	
INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	YES	NO
—						

OTHER DOCUMENTS

EXAMINER		
INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
—	1. C.S. Kim et al., "Trenched Sinker LDMOSFET (TS-LDMOS) Structure for High Power Amplifier Application above 2 GHz", International Electron Devices Meeting Proceedings, 2001, pp. 40.2.1-40.2.4.	

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.